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B.Tech.(EE) PT (Sem.-3)

DIGITAL ELECTRONICS

Subject Code: BTEE-404

M.Code: 72164

Time: 3 Hrs. Max. Marks: 60

INSTRUCTION TO CANDIDATES:

- SECTION-A is COMPULSORY consisting of TEN questions carrying TWO marks each.
- 2. SECTION-B contains FIVE questions carrying FIVE marks each and students has to attempt any FOUR questions.
- 3. SECTION-C contains THREE questions carrying TEN marks each and students has to attempt any TWO questions.

SECTION-A

1. Answer briefly:

- a) What is the difference between a latch and a flip-flop?
- b) How do you specify the delay in VHDL?
- c) What is meant by a bit?
- d) Which gates are called as universal gates and what are their advantages?
- e) What are the fundamental properties of Boolean algebra?
- f) What are minterm and maxterm?
- g) What are the limitations of the Karnaugh map?
- h) What do we need to generate hardware from VHDL model?
- i) Write down the duality theorem.
- j) What is meant by Checksum?



SECTION-B

- 2. Explain interface between TTL to CMOS circuit.
- 3. Design a 4-bit BCD adder using full adder and explain its structure and compute the circuit to add 1001 and 0101. Write the sum and carry outputs of the given binary number.
- 4. Select a 4096 × 8 bit ROM memory to store a program. The memory chip has two chip select inputs and operates from a 5V d.c. power supply. How many pins are needed for the integrated circuit package? Draw a neat block diagram and label all the input and the output terminals in the ROM.
- 5. Design a 5×32 decoder using 3×8 decoder and summarize how many decoders are required for designing the circuit.
- 6. Explain the organization of ROM with suitable diagrams.

SECTION-C

- 7. A 5-bit D/A converter produces $V_{OUT} = 0.2V$ for, a digital input of 0001. Find the value of V_{out} for an input of 11111.
- 8. Write a program to implement a BCD to Excess–3 code conversion using a PLA.
- 9. Explain in detail about the working of bipolar SRAM cell and single transistor DRAM cell with neat sketches.

NOTE: Disclosure of Identity by writing Mobile No. or Making of passing request on any page of Answer Sheet will lead to UMC against the Student.

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